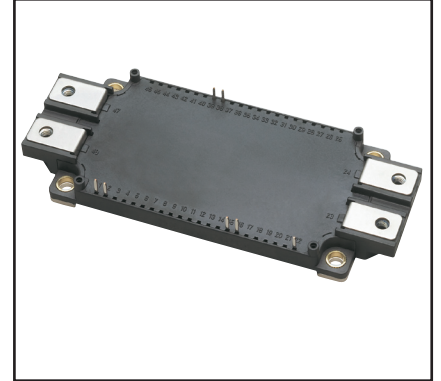
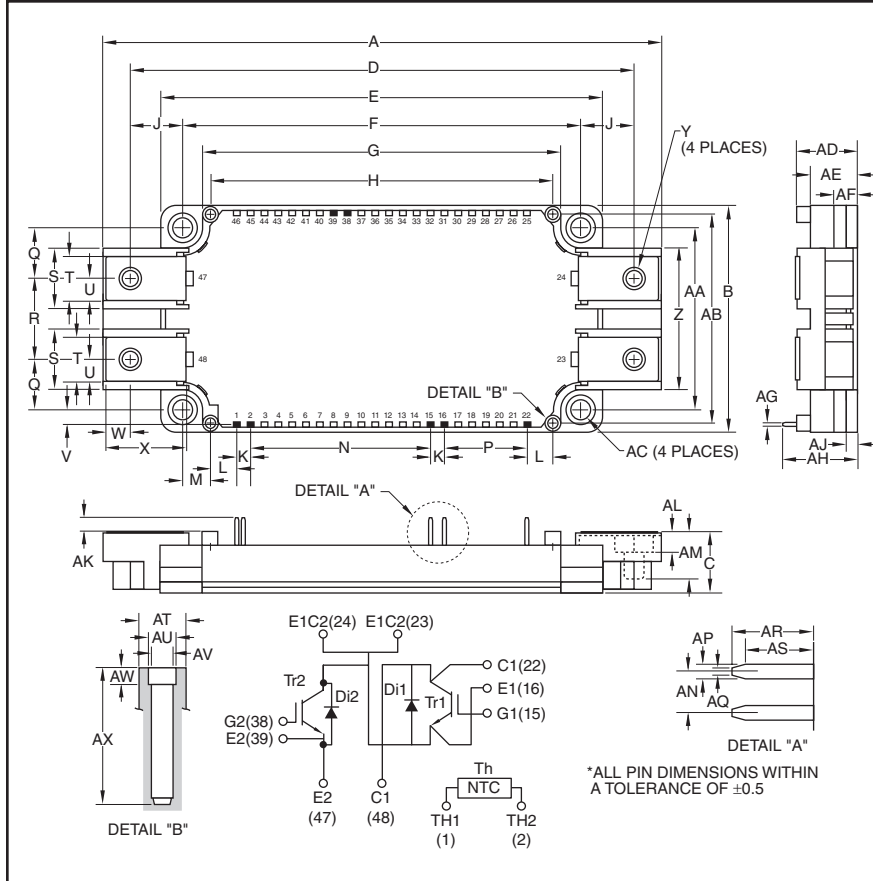


Dual IGBTMOD™ NX-Series Module 450 Amperes/1200 Volts



Description:

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of two IGBT Transistors in a half-bridge configuration with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- Low Drive Power
- Low $V_{CE(sat)}$
- Discrete Super-Fast Recovery Free-Wheel Diode
- Isolated Baseplate for Easy Heat Sinking

Applications:

- AC Motor Control
- Motion/Servo Control
- Photovoltaic/Fuel Cell

Ordering Information:

Example: Select the complete module number you desire from the table below -i.e. CM450DX-24A is a 1200V (V_{CES}), 450 Ampere Dual IGBTMOD™ Power Module.

Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	5.98	152.0
B	2.44	62.0
C	0.67	17.0
D	5.39	137.0
E	4.79	121.7
F	4.33±0.02	110.0±0.5
G	3.89	99.0
H	3.72	94.5
J	0.53	13.5
K	0.15	3.8
L	0.28	7.25
M	0.30	7.75
N	1.95	49.54
P	0.9	22.86
Q	0.55	14.0
R	0.87	22.0
S	0.67	17.0
T	0.48	12.0
U	0.24	6.0
V	0.16	4.2
W	0.37	6.5
X	0.83	21.14
Y	M6	M6

Dimensions	Inches	Millimeters
Z	1.53	39.0
AA	1.97±0.02	50.0±0.5
AB	2.26	57.5
AC	0.22 Dia.	5.5 Dia.
AD	0.67+0.04/-0.02	17.0+1.0/-0.5
AE	0.51	13.0
AF	0.27	7.0
AG	0.03	0.8
AH	0.81	20.5
AJ	0.12	3.0
AK	0.14	3.5
AL	0.21	5.4
AM	0.49	12.5
AN	0.15	3.81
AP	0.05	1.15
AQ	0.025	0.65
AR	0.29	7.4
AS	0.24	6.2
AT	0.17 Dia.	4.3 Dia.
AU	0.10 Dia.	2.5 Dia.
AV	0.08 Dia.	2.1 Dia.
AW	0.06	1.5
AX	0.49	12.5

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	450	24

CM450DX-24A
Dual IGBTMOD™ NX-Series Module
 450 Amperes/1200 Volts

Absolute Maximum Ratings, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	CM450DX-24A	Units
Power Device Junction Temperature	T_j	-40 to 150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to 125	$^\circ\text{C}$
Mounting Torque, M5 Mounting Screws	—	31	in-lb
Mounting Torque, M6 Main Terminal Screws	—	40	in-lb
Module Weight (Typical)	—	330	Grams
Baseplate Flatness, On Centerline X, Y (See Below)	—	$\pm 0 \sim +100$	μm
Isolation Voltage, AC 1 minute, 60Hz Sinusoidal	V_{ISO}	2500	Volts

Inverter Sector

Collector-Emitter Voltage (G-E Short)	V_{CES}	1200	Volts
Gate-Emitter Voltage (C-E Short)	V_{GES}	± 20	Volts
Collector Current ($T_C = 90^\circ\text{C}$)*1	I_C	450	Amperes
Peak Collector Current*4	I_{CM}	900	Amperes
Emitter Current ($T_C = 25^\circ\text{C}$)*1*5	I_E^{*3}	450	Amperes
Peak Emitter Current (Pulse)*4	I_{EM}^{*3}	900	Amperes
Maximum Collector Dissipation ($T_C = 25^\circ\text{C}$)*1*5	P_C	2840	Watts

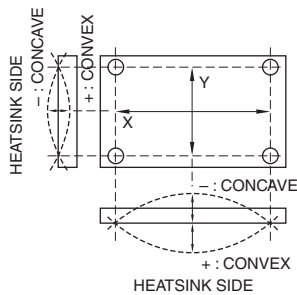
*1 Case temperature (T_C) and heatsink temperature (T_f) are defined on the surface of the baseplate and heatsink at just under the chip.

*3 I_E , I_{EM} , V_{EC} , t_{rr} and Q_{rr} represent ratings and characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

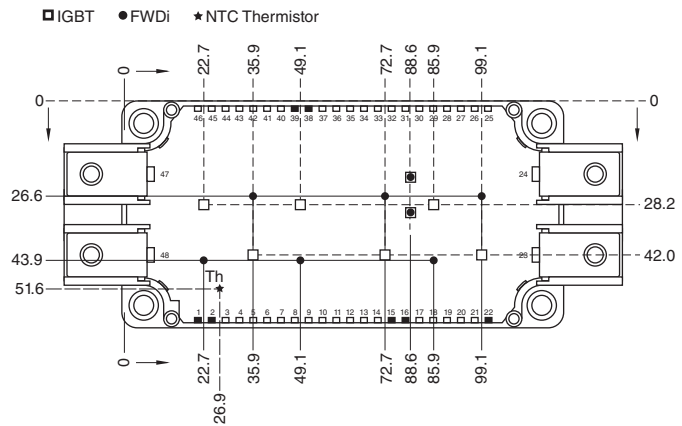
*4 Pulse width and repetition rate should be such that device junction temperature (T_j) does not exceed $T_{j(max)}$ rating.

*5 Junction temperature (T_j) should not increase beyond $T_{j(max)}$ rating.

BASEPLATE FLATNESS MEASUREMENT POINT



CHIP LOCATION (TOP VIEW)



Dimensions in mm (Tolerance: $\pm 1\text{mm}$)

CM450DX-24A
Dual IGBTMOD™ NX-Series Module
 450 Amperes/1200 Volts

Electrical and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Inverter Sector

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector Cutoff Current	I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0V$	—	—	1.0	mA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 45mA, V_{CE} = 10V$	6	7	8	Volts
Gate Leakage Current	I_{GES}	$V_{GE} = V_{GES}, V_{CE} = 0V$	—	—	0.5	μA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 450A, V_{GE} = 15V, T_j = 25^\circ\text{C}^6$	—	2.0	2.6	Volts
		$I_C = 450A, V_{GE} = 15V, T_j = 125^\circ\text{C}^6$	—	2.2	—	Volts
		$I_C = 450A, V_{GE} = 15V, \text{Chip}$	—	1.9	—	Volts
Input Capacitance	C_{ies}		—	—	68.0	nF
Output Capacitance	C_{oes}	$V_{CE} = 10V, V_{GE} = 0V$	—	—	5.9	nF
Reverse Transfer Capacitance	C_{res}		—	—	1.4	nF
Total Gate Charge	Q_G	$V_{CC} = 600V, I_C = 450A, V_{GE} = 15V$	—	2000	—	nC
Inductive	Turn-on Delay Time	$t_{d(on)}$	—	—	650	ns
Load	Turn-on Rise Time	t_r	$V_{CC} = 600V, I_C = 450A,$		250	ns
Switch	Turn-off Delay Time	$t_{d(off)}$	$V_{GE} = \pm 15V,$		700	ns
Time	Turn-off Fall Time	t_f	$R_G = 0.68\Omega, I_E = 450A,$		600	ns
Reverse Recovery Time	t_{rr}^3	Inductive Load Switching Operation	—	—	250	ns
Reverse Recovery Charge	Q_{rr}^3		—	14	—	μC
Emitter-Collector Voltage	V_{EC}^3	$I_E = 450A, V_{GE} = 0V^6$	—	2.6	3.4	Volts
		$I_E = 450A, V_{GE} = 0V, \text{Chip}$	—	2.5	—	Volts

Thermal and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Module Lead Resistance	R_{lead}	Main Terminals-Chip (Per Switch)	—	0.8	—	m Ω
Thermal Resistance, Junction to Case ^{*1}	$R_{th(j-c)Q}$	Per IGBT	—	—	0.044	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case ^{*1}	$R_{th(j-c)D}$	Per FWDi	—	—	0.078	$^\circ\text{C/W}$
Contact Thermal Resistance ^{*1}	$R_{th(c-f)}$	Case to Heatsink (Per 1 Module) Thermal Grease Applied ^{*2}	—	0.015	—	$^\circ\text{C/W}$
Internal Gate Resistance	R_{Gint}	$T_C = 25^\circ\text{C}$	1.4	2.0	2.6	Ω
		$T_C = 125^\circ\text{C}$	2.8	3.0	5.2	Ω
External Gate Resistance	R_G		0.68	—	6.8	Ω

NTC Thermistor Sector, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Zero Power Resistance	R	$T_C = 25^\circ\text{C}$	4.85	5.00	5.15	k Ω
Deviation of Resistance	$\Delta R/R$	$T_C = 100^\circ\text{C}, R_{100} = 493\Omega$	-7.3	—	+7.8	%
B Constant	$B_{(25/50)}$	$B = (\ln R_1 - \ln R_2) / (1/T_1 - 1/T_2)^{17}$	—	3375	—	K
Power Dissipation	P_{25}	$T_C = 25^\circ\text{C}$	—	—	10	mW

*1 Case temperature (T_C) and heatsink temperature (T_f) are defined on the surface of the baseplate and heatsink at just under the chip.

*2 Typical value is measured by using thermally conductive grease of $\lambda = 0.9 \text{ [W/(m} \cdot \text{K)]}$.

*3 $I_E, I_{EM}, V_{EC}, t_{rr}$ and Q_{rr} represent ratings and characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

*6 Pulse width and repetition rate should be such as to cause negligible temperature rise.

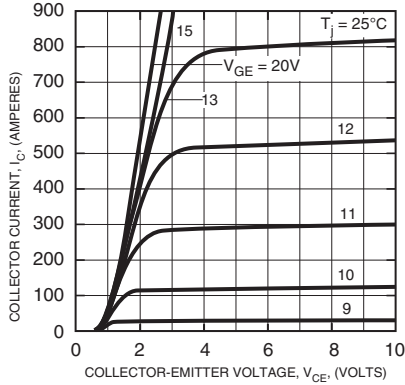
*7 R_1 : Resistance at Absolute Temperature $T_1(K)$, R_2 : Resistance at Absolute Temperature $T_2(K)$, $T(K) = T(^\circ\text{C}) + 273.15$



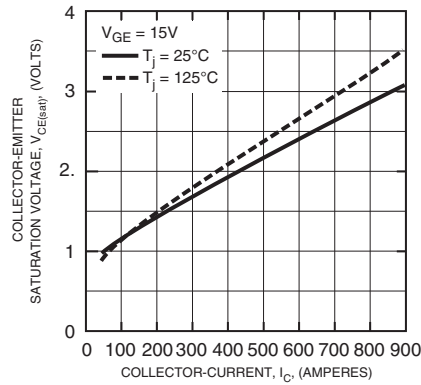
Powerex, Inc., 173 Pavilion Lane, Youngwood, Pennsylvania 15697 (724) 925-7272

CM450DX-24A
Dual IGBTMOD™ NX-Series Module
 450 Amperes/1200 Volts

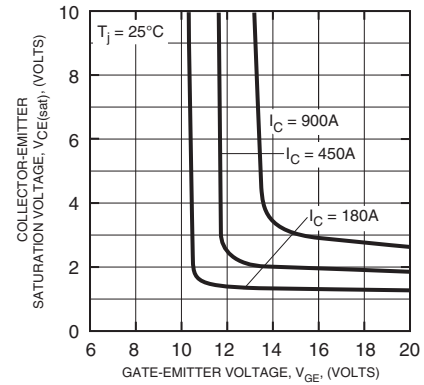
**OUTPUT CHARACTERISTICS
 (INVERTER PART - TYPICAL)**



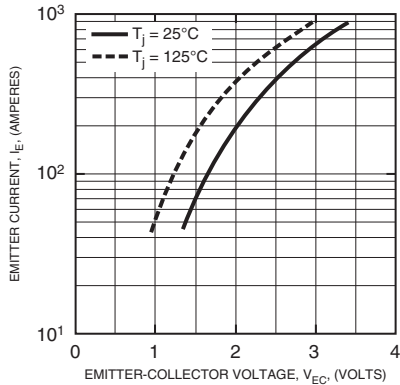
**COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS
 (INVERTER PART - TYPICAL)**



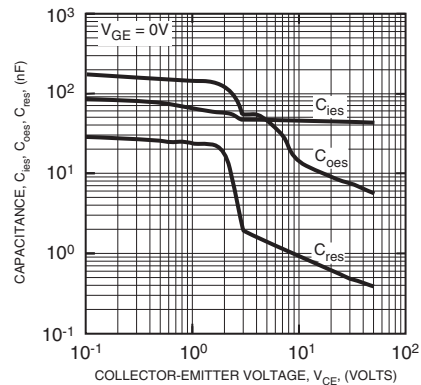
**COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS
 (INVERTER PART - TYPICAL)**



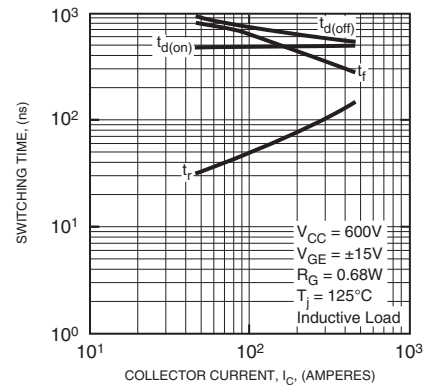
**FREE-WHEEL DIODE FORWARD CHARACTERISTICS
 (INVERTER PART - TYPICAL)**



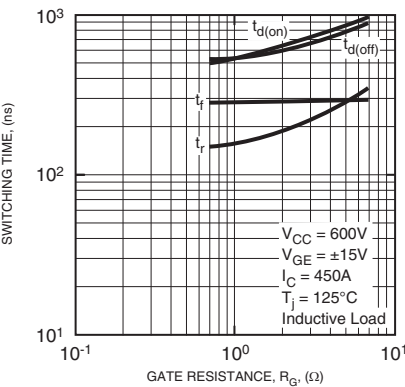
**CAPACITANCE VS. VCE
 (INVERTER PART - TYPICAL)**



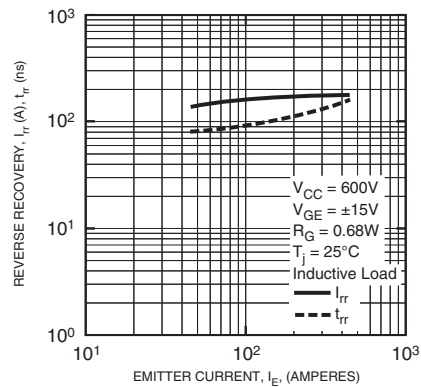
**HALF-BRIDGE SWITCHING CHARACTERISTICS
 (INVERTER PART - TYPICAL)**



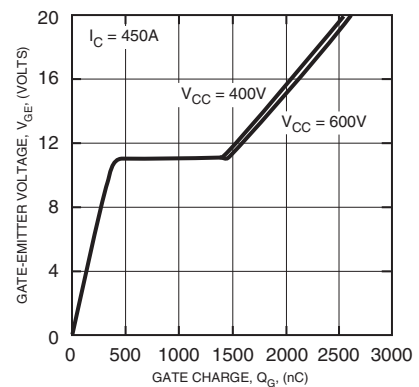
**SWITCHING TIME VS. GATE RESISTANCE
 (INVERTER PART - TYPICAL)**



**REVERSE RECOVERY CHARACTERISTICS
 (INVERTER PART - TYPICAL)**



**GATE CHARGE VS. VGE
 (INVERTER PART)**



CM450DX-24A
Dual IGBTMOD™ NX-Series Module
 450 Amperes/1200 Volts

